

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB40-28S is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB0}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W

PACKAGE STYLE .380 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10727

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$		35			V
BV_{CES}	$I_C = 200\text{ mA}$		65			V
BV_{CB0}	$I_C = 10\text{ mA}$		65			V
BV_{EBO}	$I_E = 10\text{ mA}$		4.0			V
I_{CES}	$V_{CE} = 30\text{ V}$				10	mA
I_{CB0}	$V_{CB} = 30\text{ V}$				1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 500\text{ mA}$	5.0		200	---
C_{ob}	$V_{CB} = 30\text{ V}$	$f = 1.0\text{ MHz}$			65	pF
P_G	$V_{CE} = 28\text{ V}$	$P_{IN} = 7.0\text{ W}$	7.6			dB
η_C			60			%

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.